



Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners



Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	35	V
Forward current		I_F	100	mA
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55...+150	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

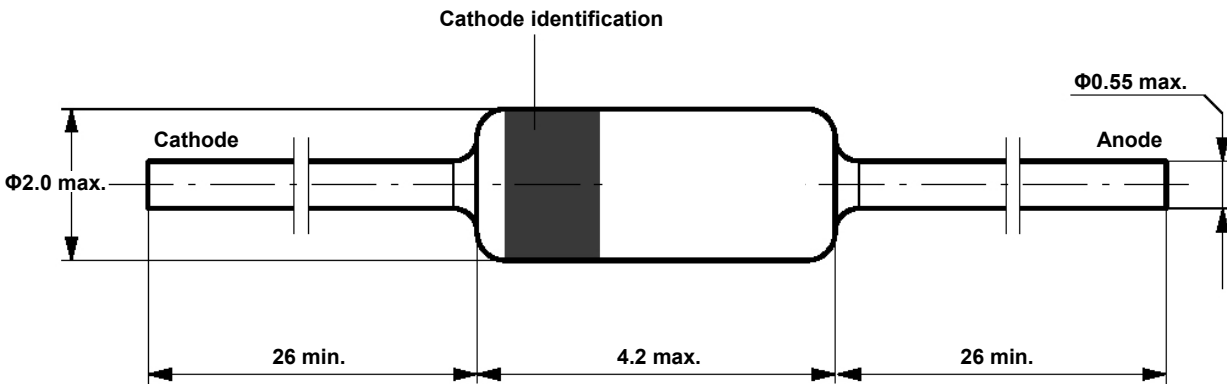


Electrical Characteristics

T_j=25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =100mA		V _F			1	V
Reverse current	V _R =20V		I _R			50	nA
Diode capacitance	f=100MHz, V _R =1V		C _D			1.5	pF
	f=100MHz, V _R =3V	BA282	C _D			1.25	pF
Differential forward resistance	f=200MHz, I _F =3mA	BA282	r _f			0.7	Ω
		BA283	r _f			1.2	Ω
	f=200MHz, I _F =10mA	BA282	r _f			0.5	Ω
		BA283	r _f			0.9	Ω
Reverse impedance	f=100MHz, V _R =1V		z _r	100			KΩ

Dimensions in mm



Standard Glass Case
JEDEC DO-35